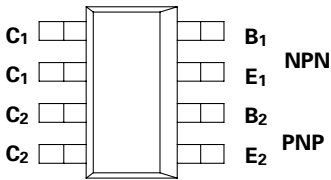


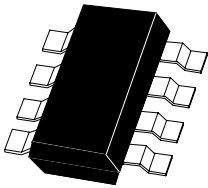
SM-8 COMPLEMENTARY MEDIUM POWER
TRANSISTORS

ISSUE 1 - NOVEMBER 1995

ZDT6757



PARTMARKING DETAIL – T6757



SM-8
(8 LEAD SOT223)

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	NPN	PNP	UNIT
Collector-Base Voltage	V_{CBO}	300	-300	V
Collector-Emitter Voltage	V_{CEO}	300	-300	V
Emitter-Base Voltage	V_{EBO}	5	-5	V
Peak Pulse Current	I_{CM}	1	-1	A
Continuous Collector Current	I_C	0.5	-0.5	A
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150		°C

THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	VALUE	UNIT
Total Power Dissipation at $T_{amb} = 25^{\circ}C^*$	P_{tot}		
Any single die "on"		2.25	W
Both die "on" equally		2.75	W
Derate above $25^{\circ}C^*$			
Any single die "on"		18	mW/°C
Both die "on" equally		22	mW/°C
Thermal Resistance - Junction to Ambient*			
Any single die "on"		55.6	°C/W
Both die "on" equally		45.5	°C/W

* The power which can be dissipated assuming the device is mounted in a typical manner on a PCB with copper equal to 2 inches square.

ZDT6757

NPN TRANSISTOR ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	300			V	$I_C=100\mu\text{A}$, $I_E=0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	300			V	$I_C=10\text{mA}$, $I_B=0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5			V	$I_E=100\mu\text{A}$, $I_C=0$
Collector Cutoff Current	I_{CBO}			100	nA	$V_{CB}=200\text{V}$, $I_E=0$
Emitter Cutoff Current	I_{EBO}			100	nA	$V_{EB}=3\text{V}$, $I_C=0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.5	V	$I_C=100\text{mA}$, $I_B=10\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			1	V	$I_C=100\text{mA}$, $I_B=10\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$			1	V	$I_C=100\text{mA}$, $V_{CE}=5\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	50 40				$I_C=100\text{mA}$, $V_{CE}=5\text{V}$ $I_C=10\text{mA}$, $V_{CE}=5\text{V}$
Transition Frequency	f_T	30			MHz	$I_C=10\text{mA}$, $V_{CE}=20\text{V}$ $f=20\text{MHz}$
Output Capacitance	C_{obo}			20	pF	$V_{CB}=20\text{V}$, $f=1\text{MHz}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

For typical characteristics graphs see FZT657 datasheet.

ZDT6757

PNP TRANSISTOR

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-300			V	$I_C = -100\mu\text{A}$, $I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-300			V	$I_C = -10\text{mA}$, $I_B = 0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E = -100\mu\text{A}$, $I_C = 0$
Collector Cutoff Current	I_{CBO}			-100	nA	$V_{CB} = -160\text{V}$, $I_E = 0$ $V_{CB} = -200\text{V}$, $I_E = 0$
Emitter Cutoff Current	I_{EBO}			-100	nA	$V_{EB} = -3\text{V}$, $I_C = 0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.5	V	$I_C = -100\text{mA}$, $I_B = -10\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-1.0	V	$I_C = -100\text{mA}$, $I_B = -10\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$			-1.0	V	$I_C = -100\text{mA}$, $V_{CE} = -5\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	50 40				$I_C = -100\text{mA}$, $V_{CE} = -5\text{V}^*$ $I_C = -10\text{mA}$, $V_{CE} = -5\text{V}^*$
Transition Frequency	f_T	30			MHz	$I_C = -10\text{mA}$, $V_{CE} = -20\text{V}$ $f = 20\text{MHz}$
Output Capacitance	C_{obo}			20	pF	$V_{CB} = -20\text{V}$, $f = 1\text{MHz}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

For typical characteristics graphs see FZT757 datasheet.